

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/591,629
Applicants: Ashutosh MISRA, et al.
Filed Internationally: February 24, 2005
US National: September 5, 2006
Title: METHOD FOR FORMING DIELECTRIC OR METALLIC FILMS
TC/A.U.: Unknown
Examiner: Unknown
Docket No.: Serie 6550 CIP
Customer No.: 40582

INFORMATION DISCLOSURE STATEMENT

Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. § 1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the non-US patent documents cited on the attached PTO Form 1449 is enclosed.

No fee is due at this time in accordance with 37 C.F.R. § 1.97. However, the Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17 and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 01-1375.

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IDS

To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner-initiated copy of this form be returned to the undersigned.

Respectfully submitted,



Brandon S. Clark
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Date: January 18, 2007

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INFORMATION DISCLOSURE CITATION (USE SEVERAL SHEETS IF NECESSARY)			ATTY. DOCKET NO. Serie 6550 CIP	SERIAL NO. 10/591,629	
			APPLICANT(S) Ashutosh MISRA, et al.		
			FILING DATE 9/5/2006	GROUP 2818	
U.S. PATENT DOCUMENTS					
Examiner Initial	Document Number	Date	Name	Class	Subclass
A1	US 5 470 398	11/28/1995	Shibuya et al.		
A2	US 2004 0198069	10/07/2004	Metzner et al.		
A3	US 2003 111678	6/19/2003	Colombo et al.		
A4	US 2003 207549	11/06/2003	Jenq		
A5	US 6 399 208	6/04/2002	Baum et al.		
FOREIGN PATENT DOCUMENTS					
	Document Number	Date	Country	Class	Subclass
B1	WO 2004 010466	1/29/2004	PCT		
B2	EP 1 028 458	8/16/2000	Europe		
B3	JP 2000 272283 & Abstract	2/19/2002	Japan		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
C1	International Search Report for PCT/IB2005/000522				
C2	Patent Abstracts of Japan, vol. 2002, no. 06, June 4, 2002 & JP 2002 053980, February 19, 2002				
C3	Ohshita, Y. et al. <i>Hf_{1-x}Si_xO₂ deposition by metal organic chemical vapor deposition using the Hf(NEt₂)₄/SiH(NEt₂)₂O₂ gas system, Preparation and Characterization</i> , Elsevier, Sequoia, NL, vol. 416, no. 1-2, September 2, 2002, pp. 208-211				
C4	Japan Journal of Applied Physics, vol. 42, no. 6A, pp. L578-L580, June 2003				
C5	Applied Physics Letters, vol. 80, no. 13, pp. 2362-2364, April 2002				
Examiner	/Arman Khosraviani/		Date Considered 04/16/2008		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

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